

# Oves Badami

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/11252045/publications.pdf>

Version: 2024-02-01

15  
papers

118  
citations

1478505

6  
h-index

1474206

9  
g-index

15  
all docs

15  
docs citations

15  
times ranked

99  
citing authors

#	ARTICLE	IF	CITATIONS
1	Study of gate current in advanced MOS architectures. Solid-State Electronics, 2022, 194, 108345.	1.4	1
2	KMC-based POM flash cell optimization and time-dependent performance investigation. Semiconductor Science and Technology, 2021, 36, 075021.	2.0	1
3	A Kinetic Monte Carlo Study of Retention Time in a POM Molecule-Based Flash Memory. IEEE Nanotechnology Magazine, 2020, 19, 704-710.	2.0	5
4	Nano-electronic Simulation Software (NESS): a flexible nano-device simulation platform. Journal of Computational Electronics, 2020, 19, 1031-1046.	2.5	20
5	Enhanced Capabilities of the Nano-Electronic Simulation Software (NESS). , 2020, , .		5
6	Physical Insights into the Transport Properties of RRAMs Based on Transition Metal Oxides. , 2019, , .		1
7	Multiscale Modeling of Charge Trapping in Molecule Based Flash Memories. , 2019, , .		2
8	Surface Roughness Scattering in NEGF using self-energy formulation. , 2019, , .		3
9	Mobility of Circular and Elliptical Si Nanowire Transistors Using a Multi-Subband 1D Formalism. IEEE Electron Device Letters, 2019, 40, 1571-1574.	3.9	15
10	Simulation of the Impact of Ionized Impurity Scattering on the Total Mobility in Si Nanowire Transistors. Materials, 2019, 12, 124.	2.9	21
11	Comprehensive Study of Cross-Section Dependent Effective Masses for Silicon Based Gate-All-Around Transistors. Applied Sciences (Switzerland), 2019, 9, 1895.	2.5	15
12	Advanced Simulation of RRAM Memory Cells. , 2019, , .		0
13	Schrödinger Equation Based Quantum Corrections in Drift-Diffusion: A Multiscale Approach. , 2019, , .		2
14	Variability Predictions for the Next Technology Generations of n-type SixGe1-x Nanowire MOSFETs. Micromachines, 2018, 9, 643.	2.9	7
15	An Improved Surface Roughness Scattering Model for Bulk, Thin-Body, and Quantum-Well MOSFETs. IEEE Transactions on Electron Devices, 2016, 63, 2306-2312.	3.0	20